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**DL5711**  
**DL6263**

**Small Signal  
Schottky Diodes**

**Features**

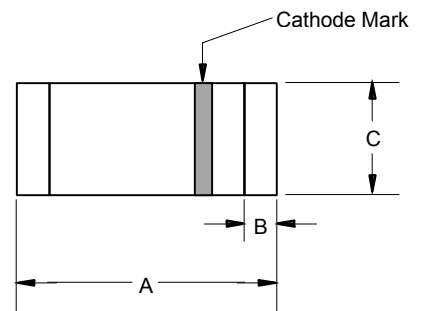
- For general purpose applications
- These diodes are also available in the DO-35 case with type designation 1N5711 and 1N6263, in the Micro-MELF case with type designation MCL5711 and MCL6263.

**Maximum Ratings**

Repetitive Peak Reverse Voltage DL5711 DL6263	$V_R$	70V 60V	
Maximum Forward Surge Current	$I_{FSM}$	2.0A	$t_p < 10\mu S, T_A = 25^\circ C$
Power Dissipation	$P_{TOT}$	400mW*	
Junction Temperature	$T_J$	125°C	
Storage Temperature Range	$T_{STG}$	-55~+150°C	

\* Valid provided that electrodes are kept at ambient temperature

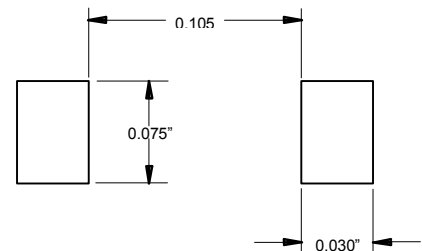
**MINIMELF**



**DIMENSION**

DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	.134	.142	3.40	3.60	
B	.008	.016	0.20	0.40	
C	.055	.059	1.40	1.50	

**SUGGESTED SOLDER PAD LAYOUT**



**Electrical Characteristics @ 25°C Unless Otherwise Specified**

Maximum Forward Voltage	$V_F$	0.41V 1.0V	$I_F = 1.0mA$ $I_F = 15mA$
Minimum Reverse Breakdown voltage DL5711 DL6263	$V_R$	70V 60V	
Maximum Leakage current	$I_R$	200nA	$V_R = 50V$
Maximum Junction Capacitance	$C_J$	2.0pF	$V_R = 0, f = 1MHz$
Maximum Reverse recovery time	$t_{rr}$	1.0ns	$I_F = 5.0mA, I_R = 5.0mA$
Maximum Thermal resistance junction to Ambient Air	$R_{\theta JA}$	0.3K/W	

# DL5711,DL6263



Fig.1 Typical variation of fwd. current vs forward. voltage for primary conduction through the Schottky barrier

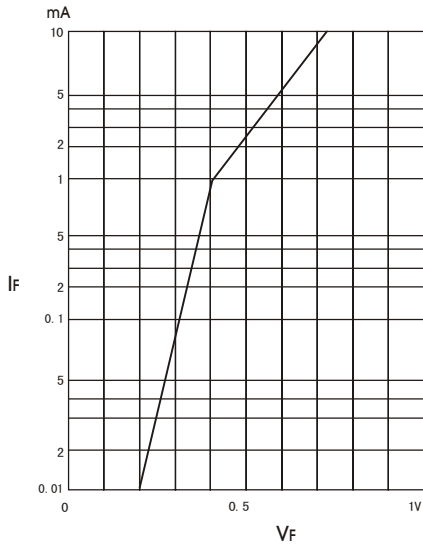


Fig.2 Typical forward conduction curve of combination Schottky barrier and PN junction guard ring

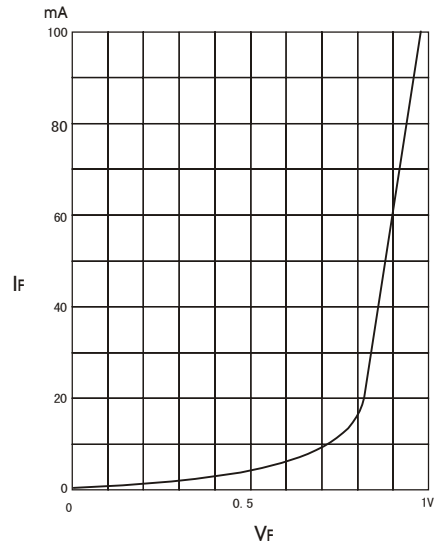


Fig.3 Typical variation of reverse current at various temperatures

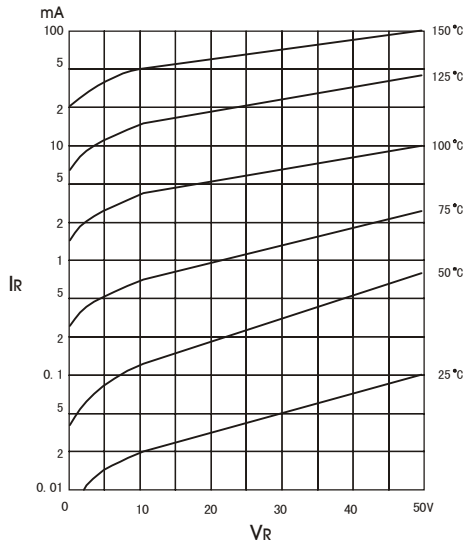


Fig.4 Typical capacitance curve as a function of reverse voltage

